

Large Spot Reflectometry for CVD Process Control

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- Project Goals
- Hardware
 - Verity SP2002 Reflectometer
 - Integration of Reflectometer on NVLS Concept Two Speed Tool
- Data and Analysis
- Summary

- Integrate low-cost film thickness measurement on CVD tool to provide film measurement on every wafer with short lag-time for
 - run-to-run feedback process control
 - excursion detection(1st part of Fault Detection and Classification (FDC))

Goals of this Project

- Integrate large-spot spectral reflectometer on Novellus Concept Two Speed CVD Tool in TI Kilby Wafer Fab
- Semi-automate data collection with no through-put hit
- Start to evaluate integrated measurement capability
 - Compare to stand-alone measurements
 - Show film thickness variance:
 - across-wafer
 - lot-to-lot
 - wafer-to-wafer,
 - chamber-to-chamber
- Minimal resource requirements from Texas Instruments and Novellus

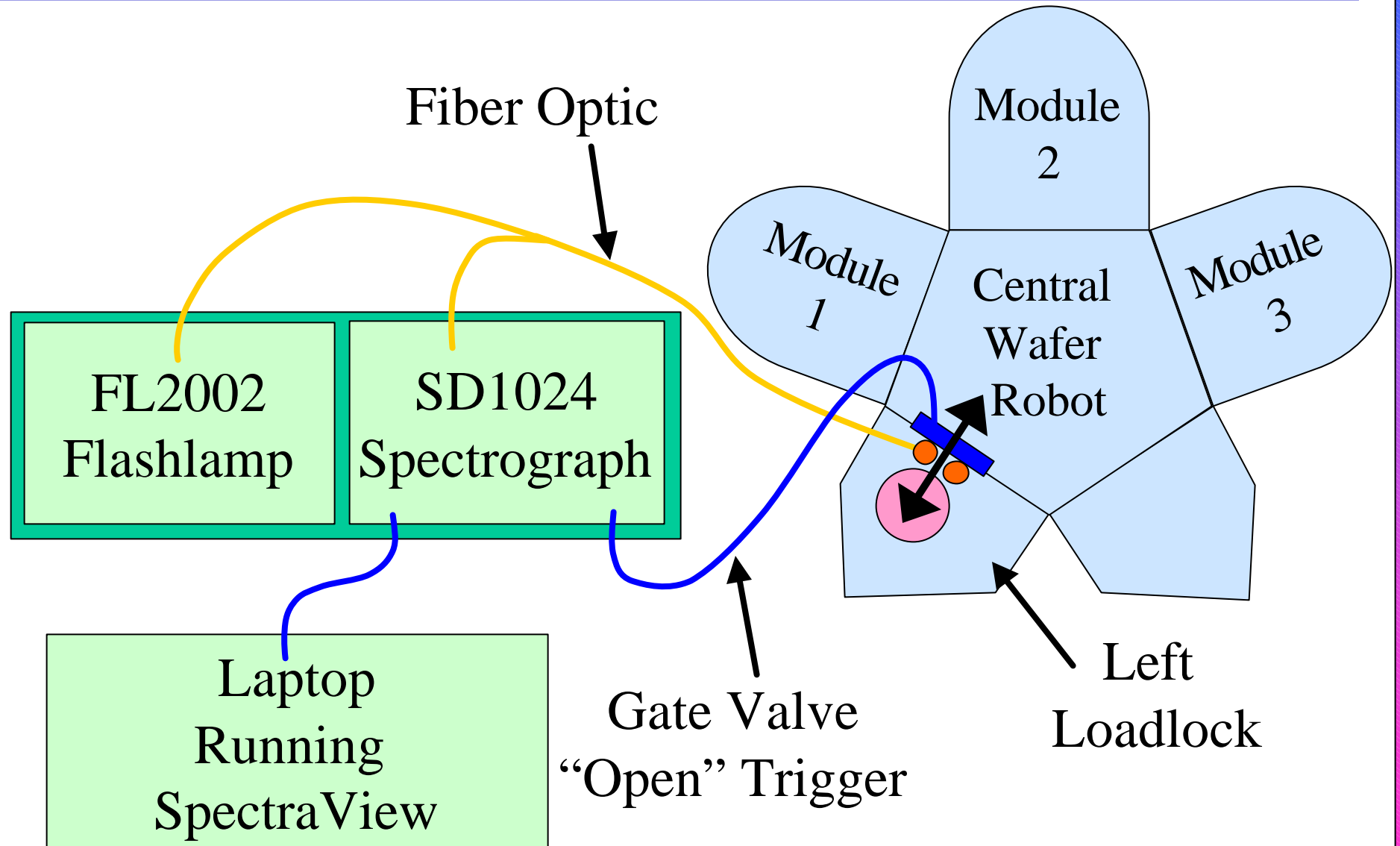
Xenon flash lamp

- broad-band light source
- short flash stops wafer motion
- synchronized with spectral data acquisition



Multichannel spectrograph
– UV- NIR (200-800nm)

System Diagram



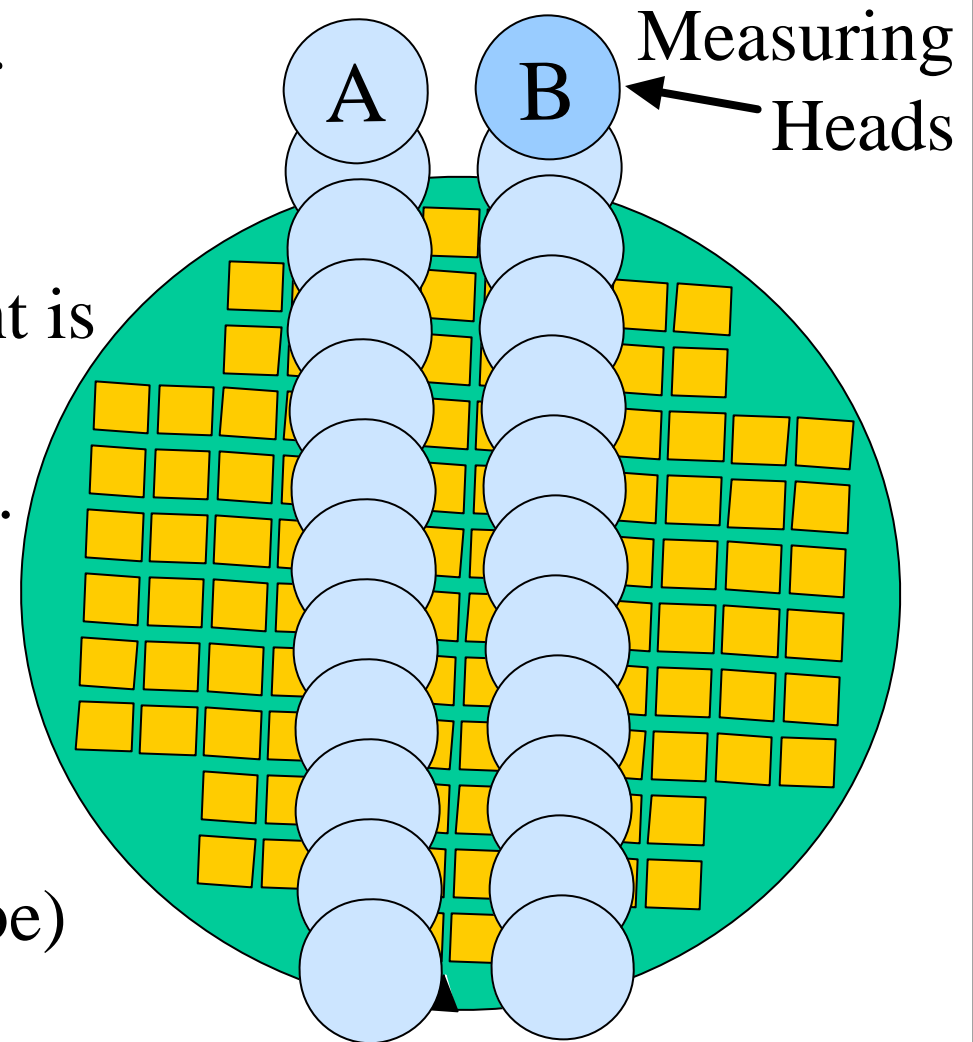
Wafer Measurements

Robot moves the wafer under the measurement heads.

Probe spot-to-wafer alignment is dependant on prior wafer alignment and robot handling.

Flashlamp sampling
-- stops wafer motion
-- flashing every 30 msec.
(12 measurements/wafer/probe)

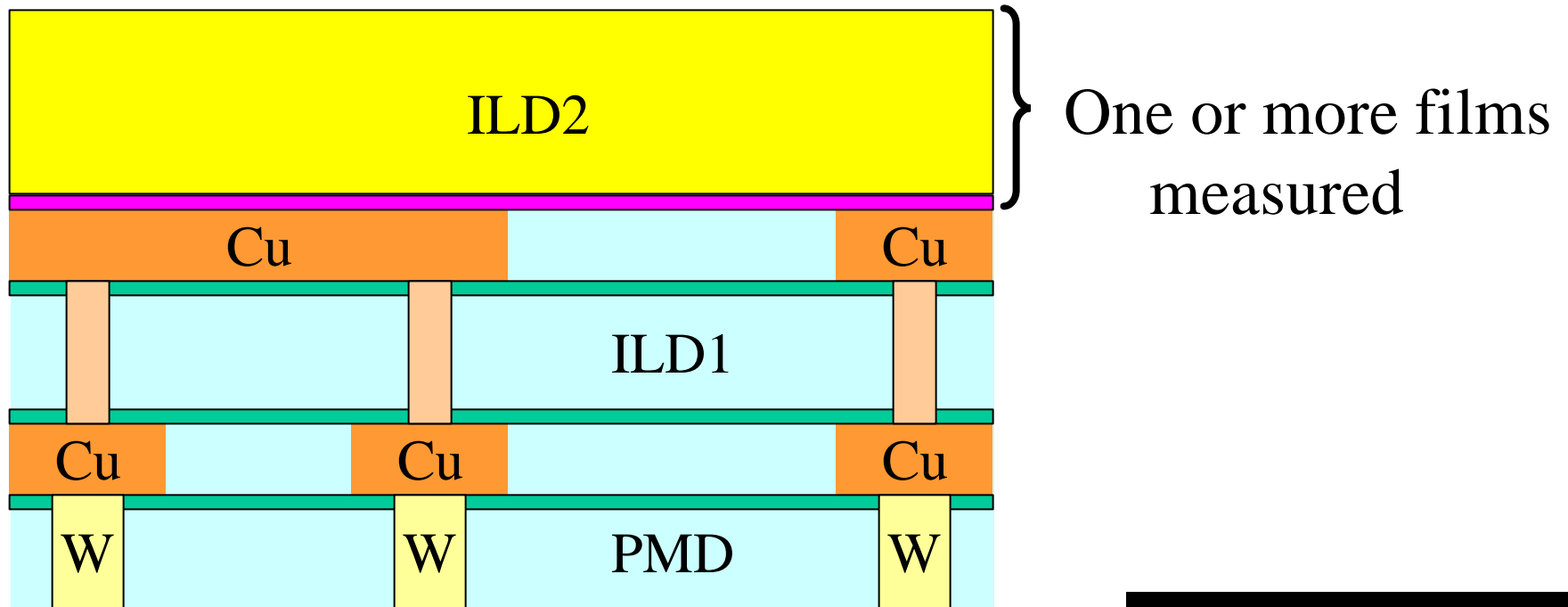
Large spot (1 in. dia.) for die-scale averaging



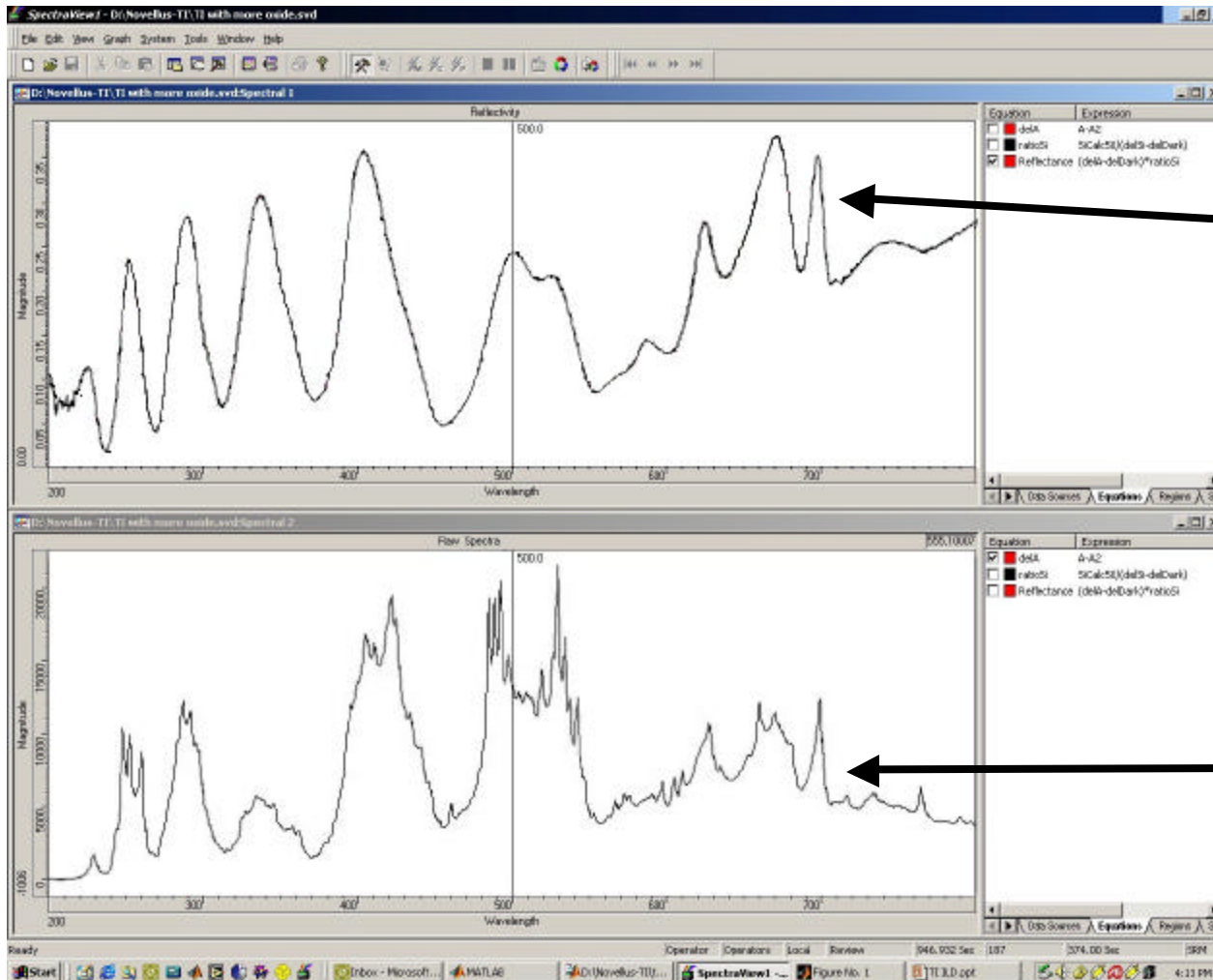
Wafer Structure

Minimum information required

- Uppermost ILD stack structure
- Nominal thickness
- Film optical indices



SpectraView Data



Normalized
Reflectivity
Data

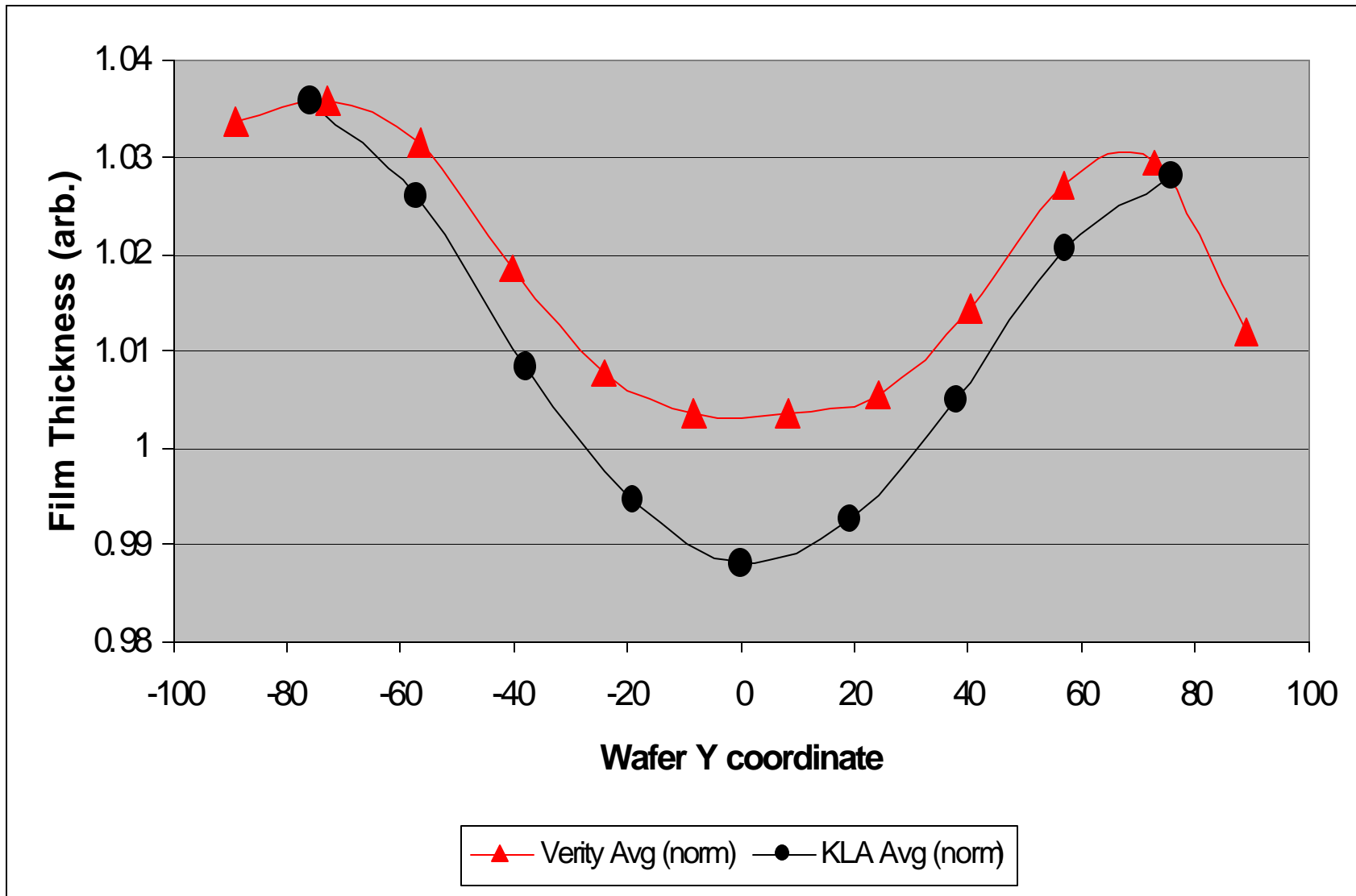
Raw
Data

- Algorithm applied to
 - **Inputs :**
 - Normalized reflectometry data
 - Film stack description
 - Film material optical indices
 - Nominal thicknesses
 - **Outputs:**
 - Measured thicknesses

Some algorithm optimization is required for different ILD layers

- Correlating the thickness measurements with wafer and chamber processing information yields film thickness average and variance
 - Across the wafer
 - Wafer-to-wafer
 - Lot-to-lot
 - Chamber-to-chamber
- Study variables
 - Die size
 - Film thicknesses
 - ILD levels
 - ILD materials

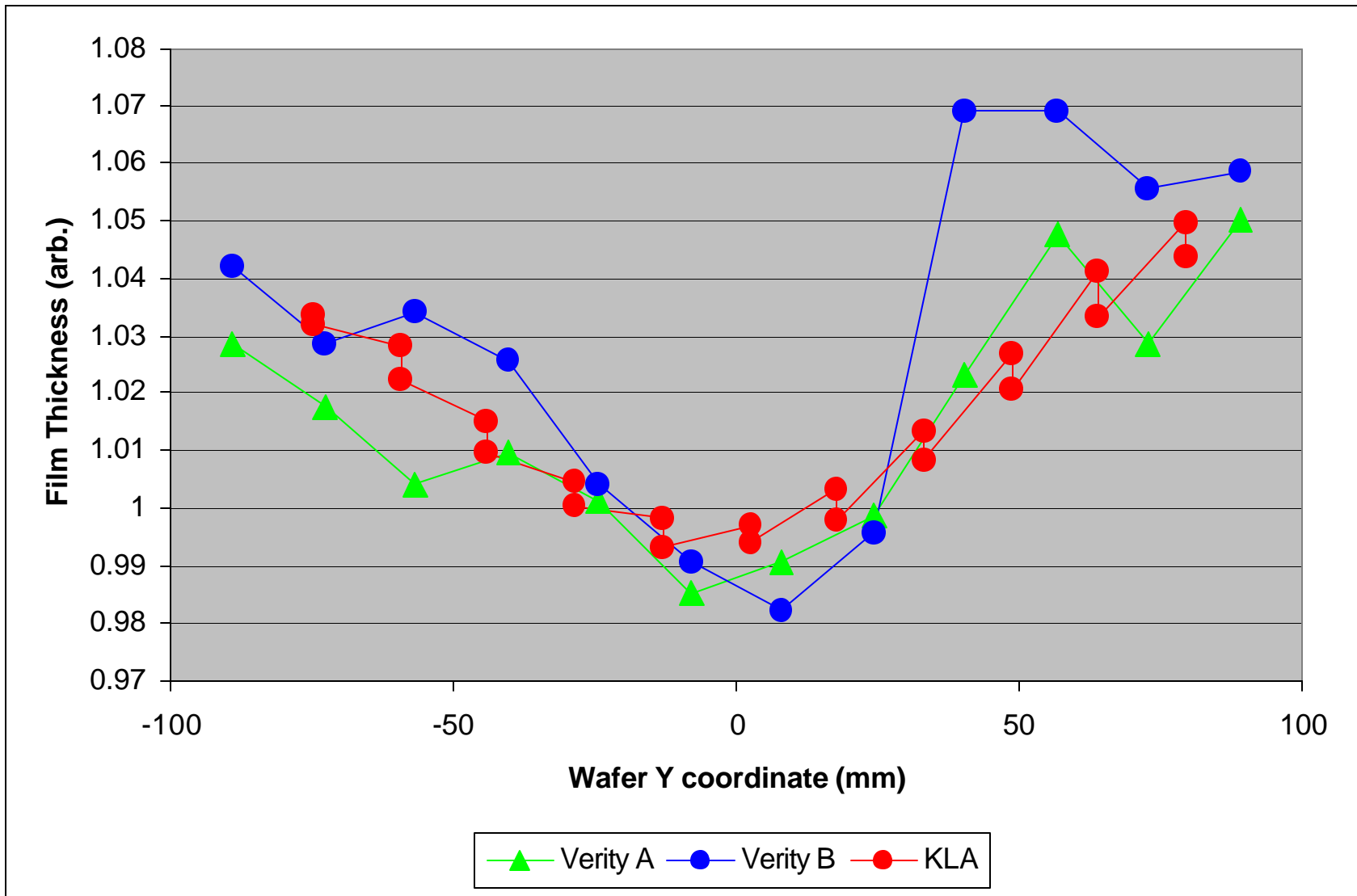
Pilot Wafer (ILD Film on Si)



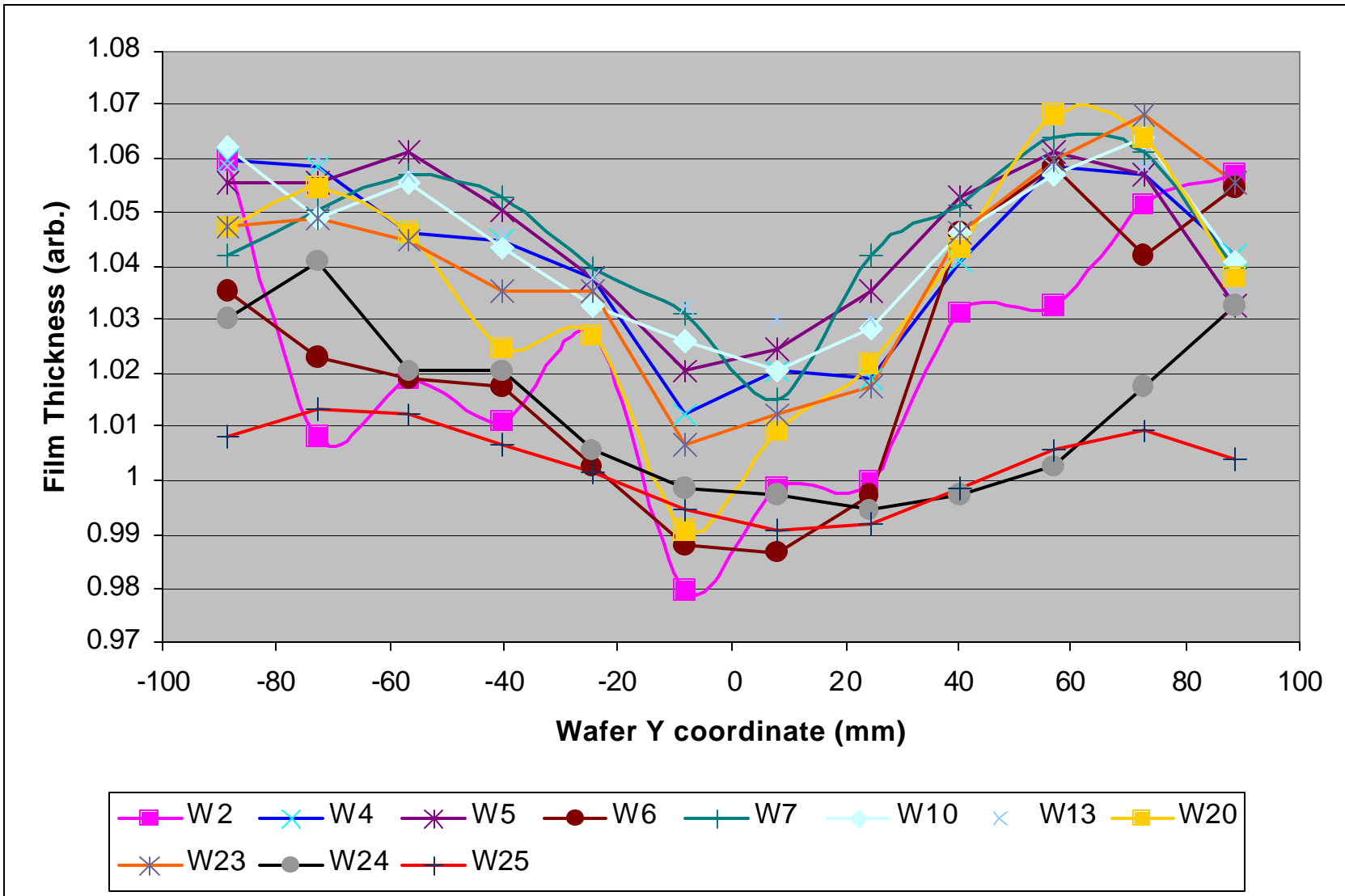
ILD over Tungsten Plug

- Study variables
 - Die size < 5 x 5 mm
 - ILD level = Contact
 - Dielectric deposition on nitride over patterned tungsten plugs
 - ILD material = FSG

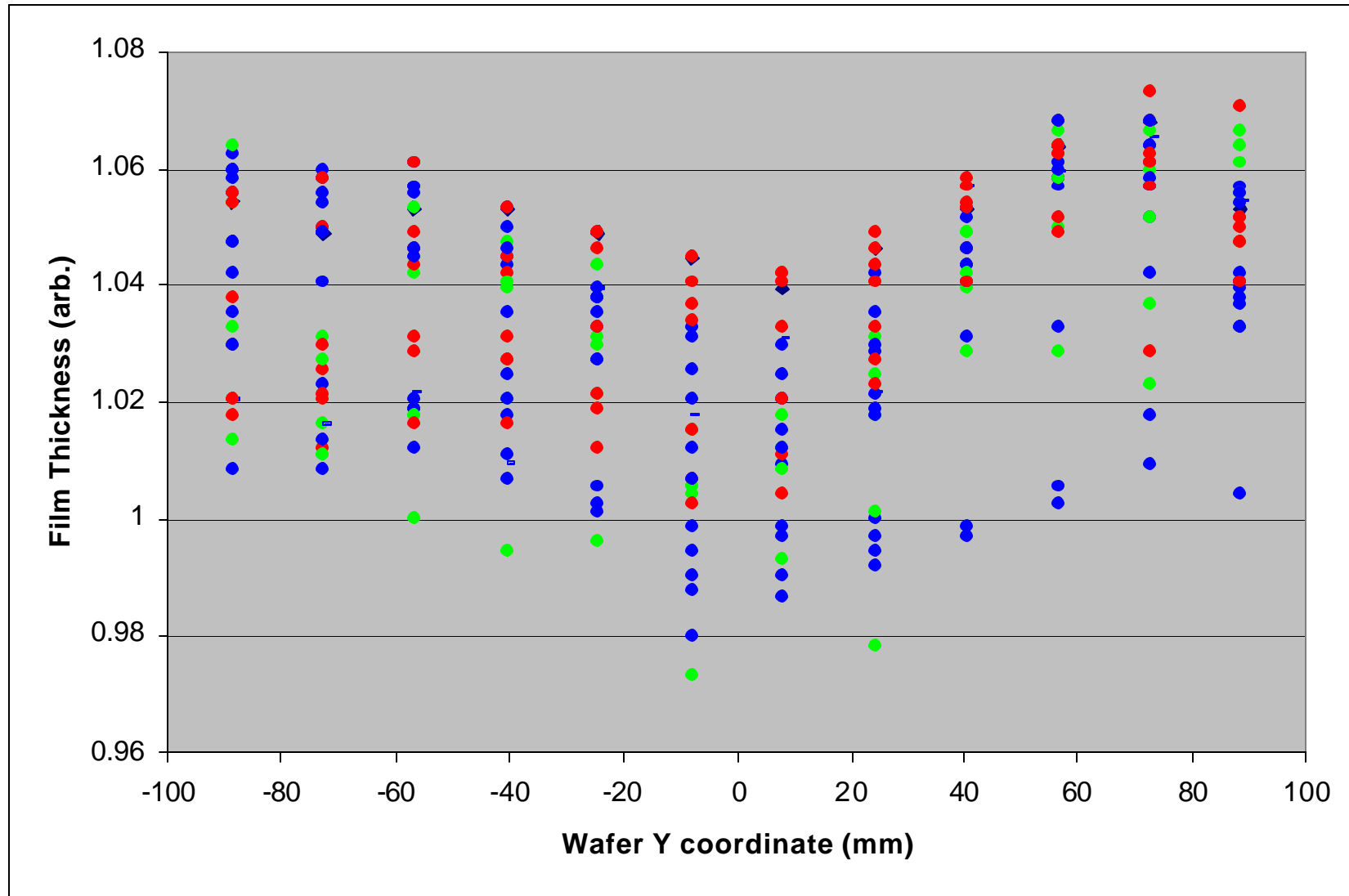
WIW Variation



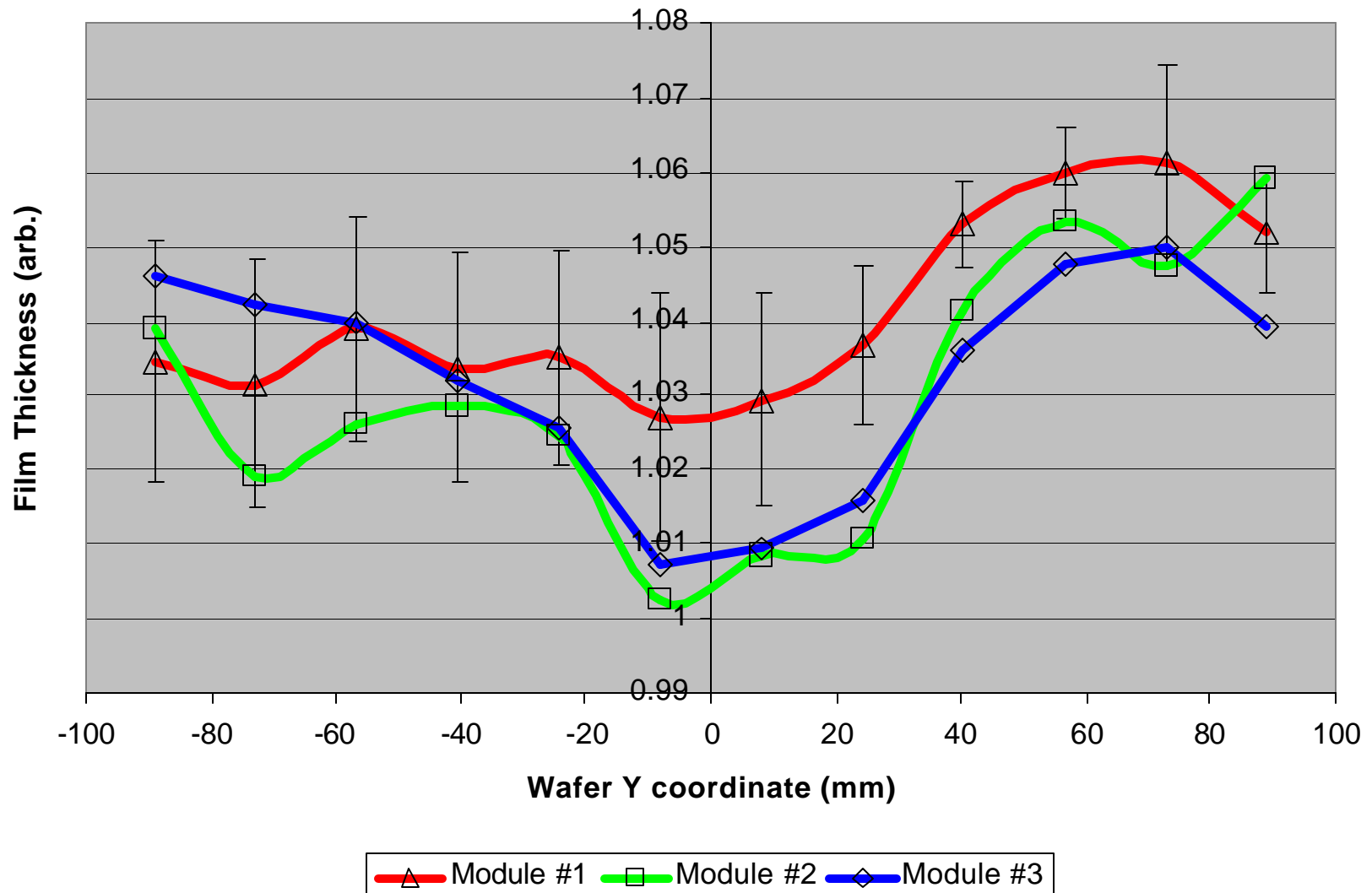
W2W Variation of Module #3



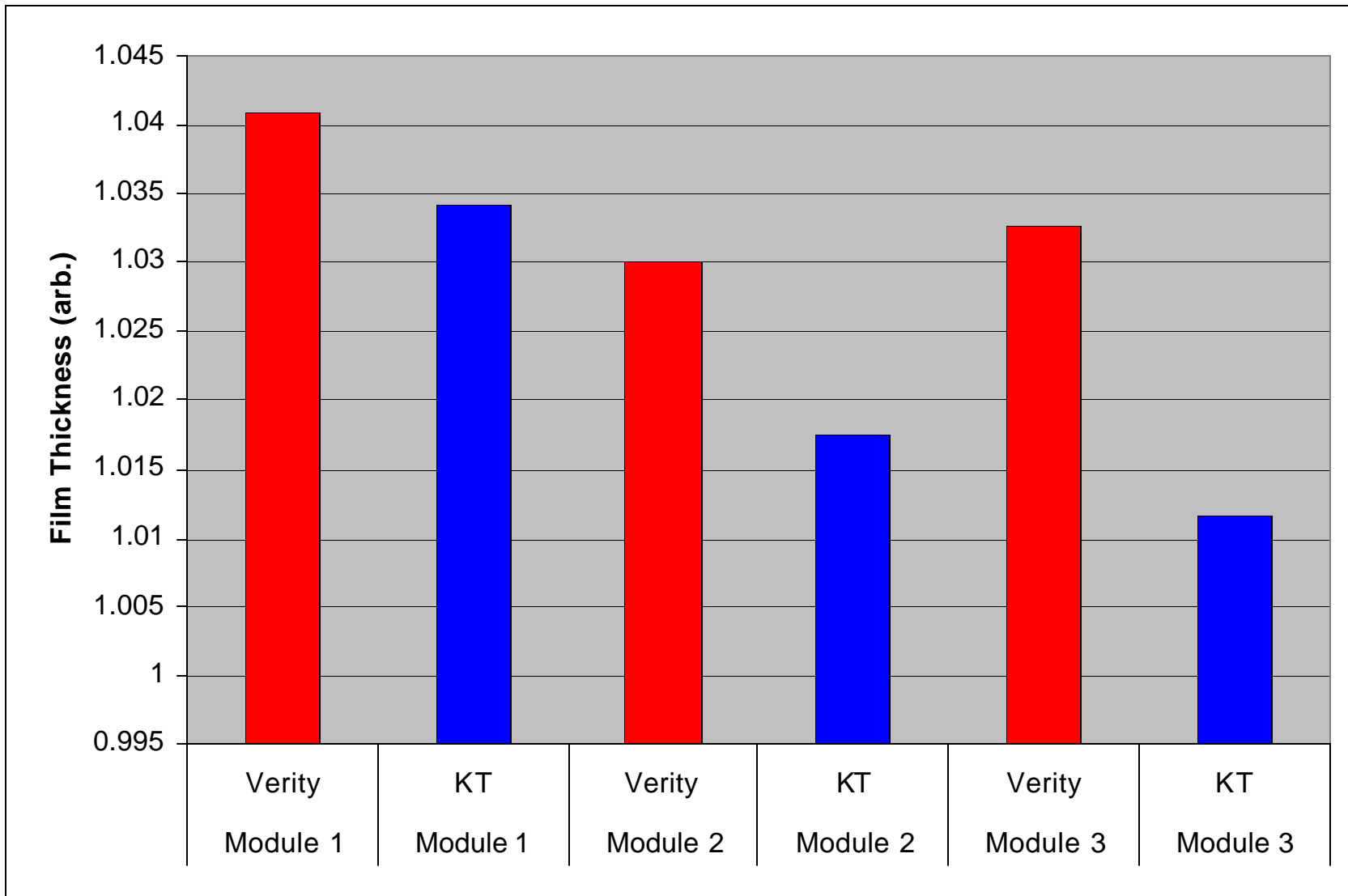
Within Lot Variation



Variation of 3 Modules



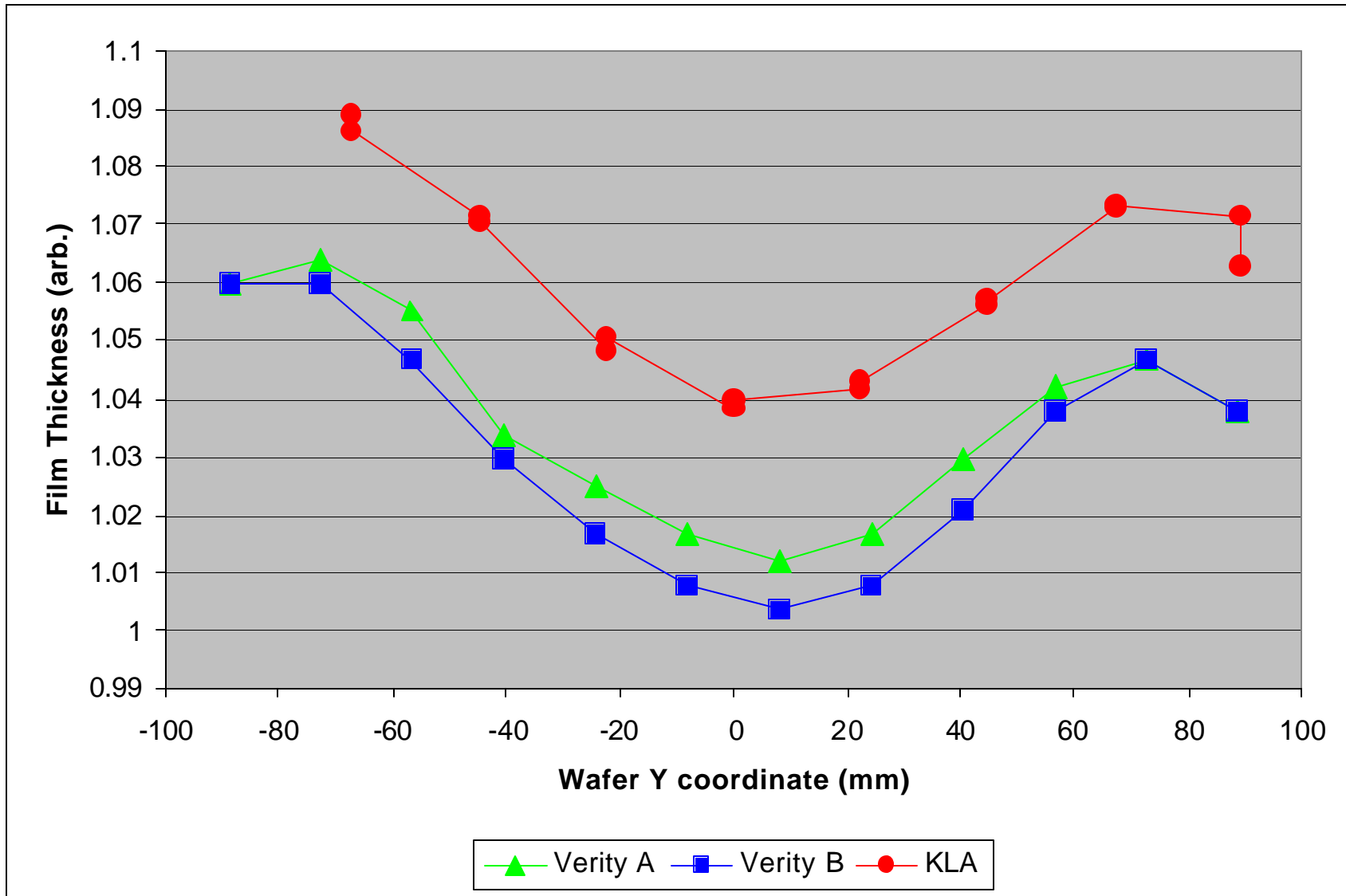
Average Wafer Variation



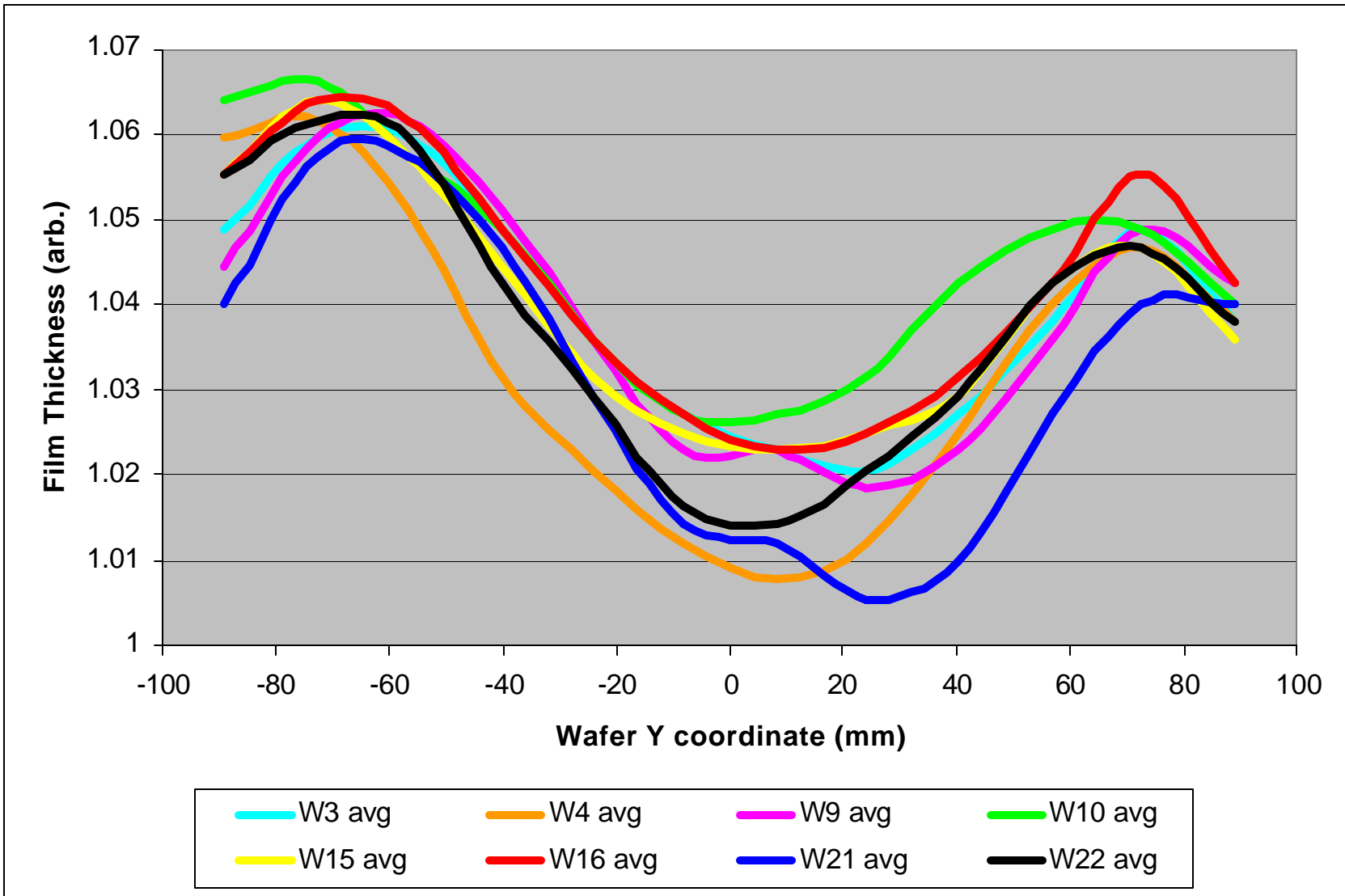
ILD over Copper Damascene

- Study variables
 - Die size < 10 x 10 mm
 - ILD level = ILD-5
 - Dielectric deposition on nitride over planarized copper Damascene
 - ILD material = FSG

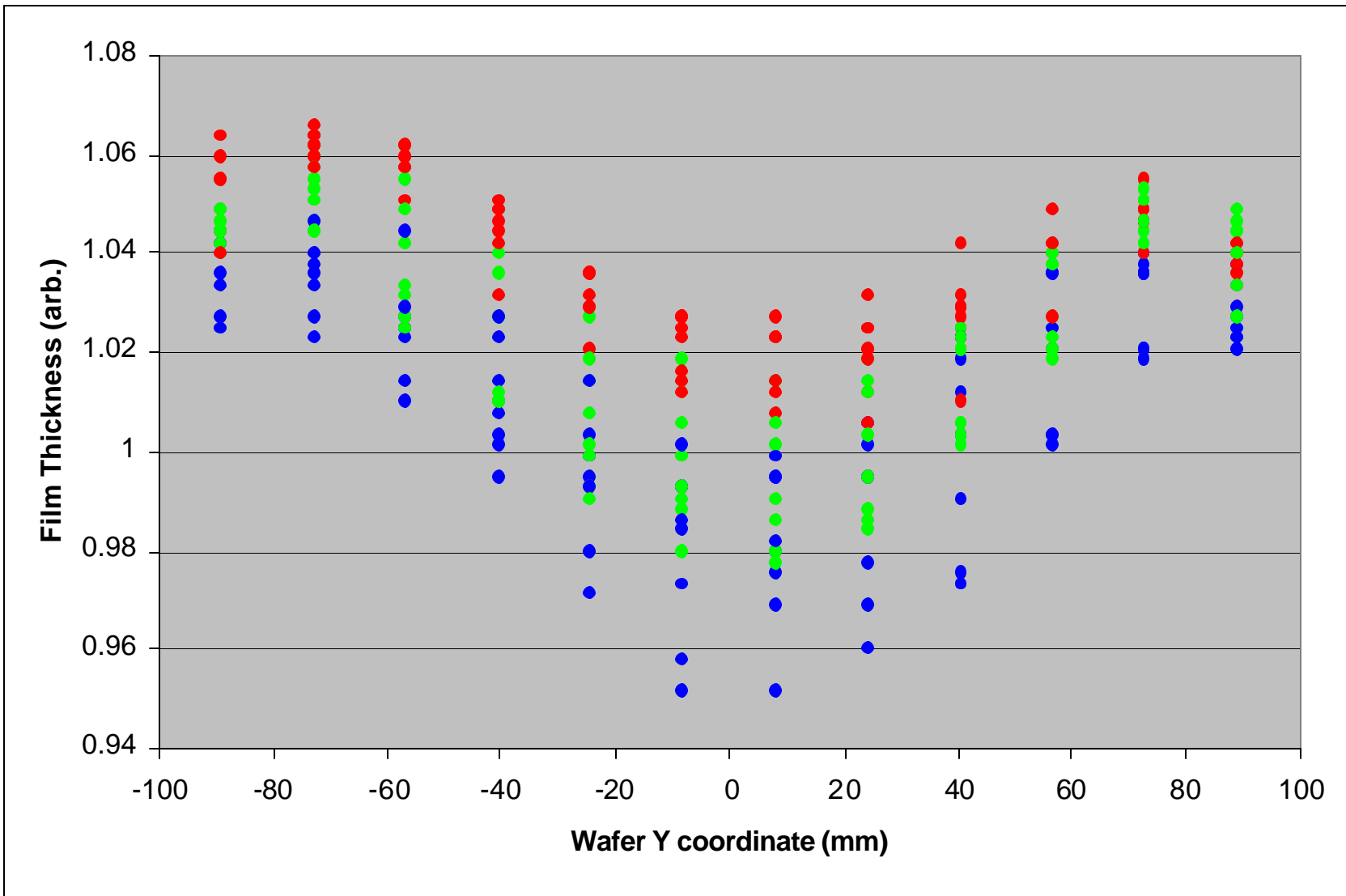
WIW Variation



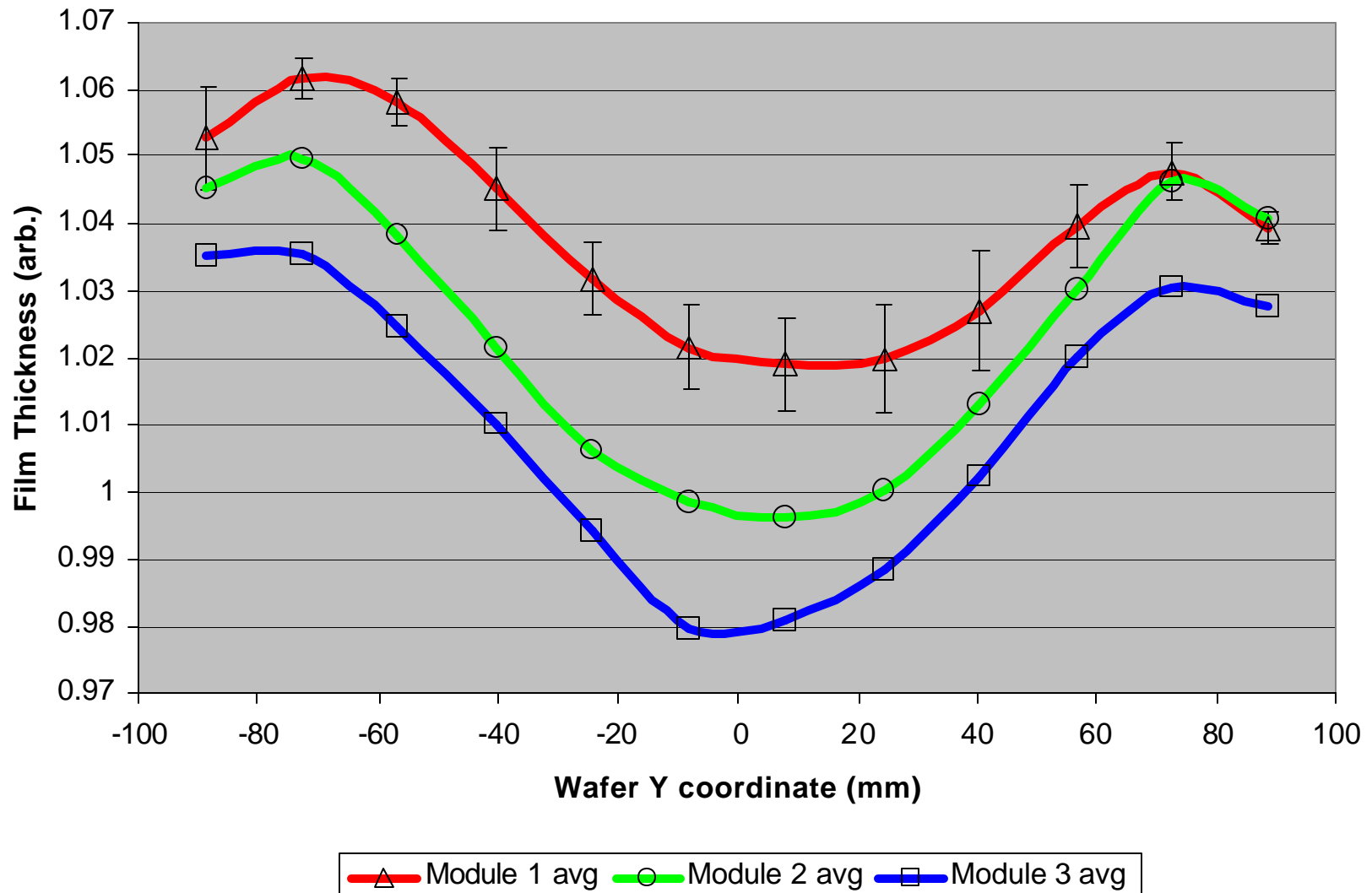
W2W Variation of Module #1



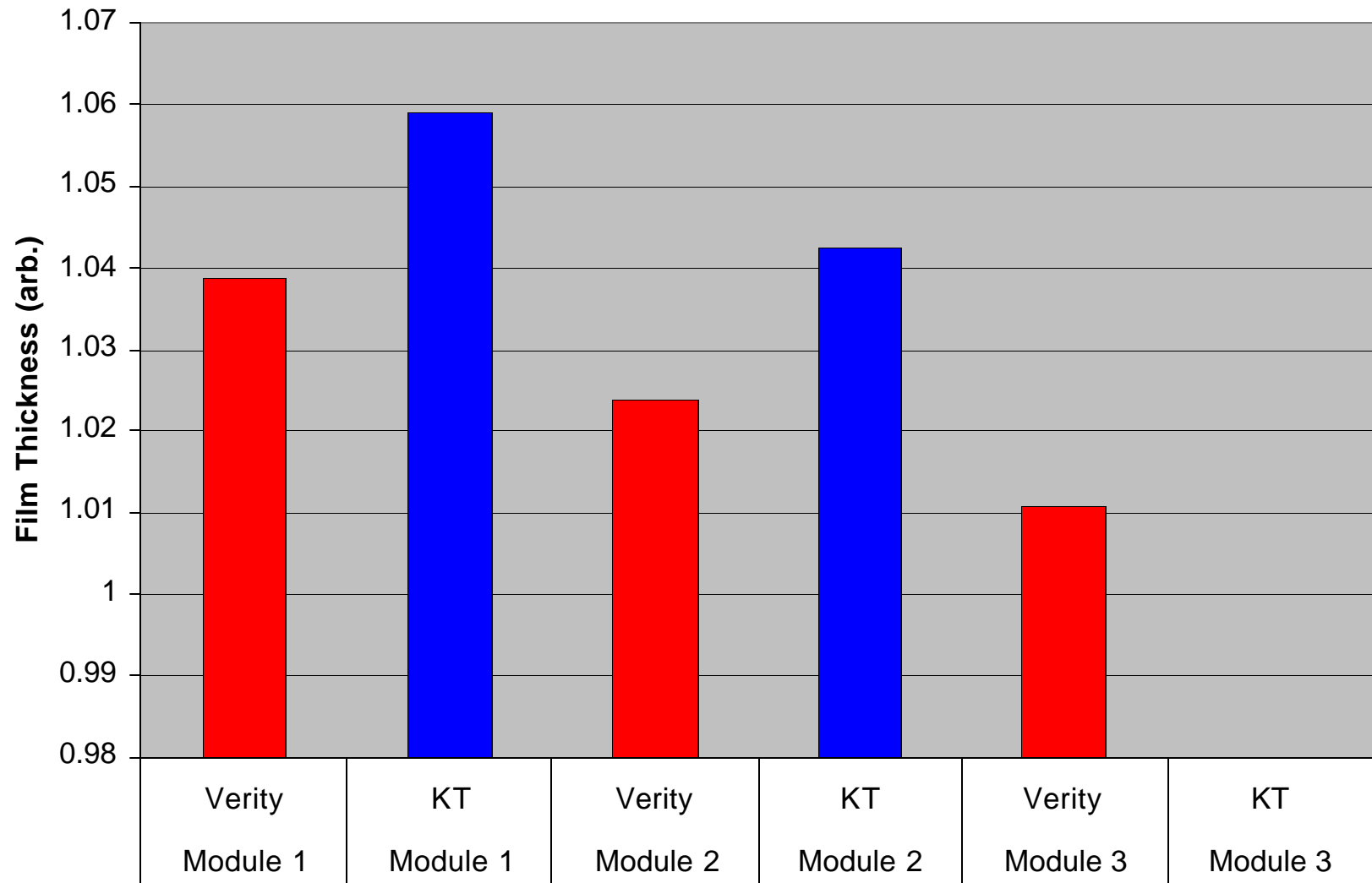
Within Lot Variation



Variation of 3 Modules



Average Wafer Variation



- No impact on through-put
- Film thickness profile measurements *on every wafer* increases visibility on the process
 - Average thickness
 - Thickness profile map
 - Chamber matching
 - Basis for lot statistics
 - Measuring product wafers can reduce the number of test wafers
- Short lag-time enables new capabilities
 - Run-to-run feedback process control
 - Rapid excursion detection

- Eliminate or reduce monitor wafers
 - **Process more product wafers**
 - **Increase fab revenue**
- Monitor and track performance variance between specific process modules -- not just the average of a 3-module process tool
 - **Improves “tool” matching**
- Detect onset of tool and/or process excursion(s)
 - **Save several lots from being misprocessed**
 - **Improve yield**
 - **Reduce tool CoO**
- Facilitates quick insertion of process module into process line after maintenance work
 - **Reduce downtime**
 - **Reduce tool CoO**
- Replace some scheduled maintenance with “need-based” maintenance
 - **Reduce downtime**
 - **Process more product wafers**

- Large-spot spectral reflectometry integrated on CVD tools provides useful film thickness measurement information
 - Faster test wafer measurement
 - Measurement of patterned wafers to reduce test wafers
 - Short measurement lag-time for feedback process control
 - Rapid excursion detection (1st half of FDC)
- Integrated on Novellus tool
 - Opto-mechanical interface is satisfactory for now
 - Sensor-Tool coordination needs improvement
- Rigorous gauge study is required next